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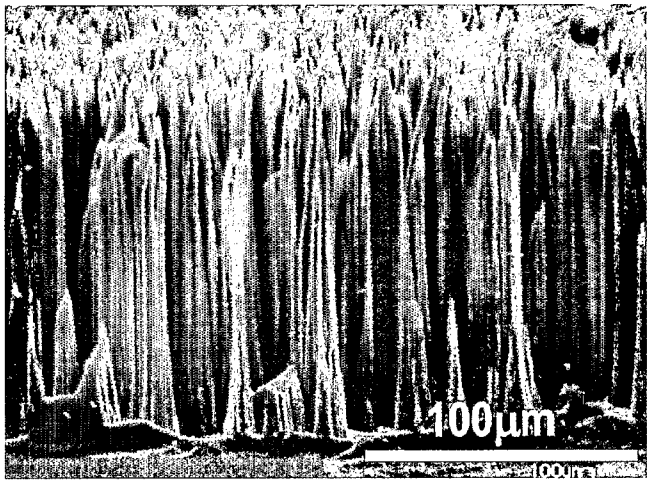
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(54) **Title:** METHODS FOR PROTECTING SILICON OR SILICON CARBIDE ELECTRODE SURFACES FROM MORPHOLOGICAL MODIFICATION DURING PLASMA ETCH PROCESSING



(57) **Abstract:** Methods for forming a protective polymeric coating on a silicon or silicon-carbide electrode of a plasma processing chamber are provided. The polymeric coating provides protection to the underlying surface of the electrode with respect to exposure to constituents of plasma and gaseous reactants. The methods can be performed during a process of cleaning the chamber, or during a process for etching a semiconductor substrate in the chamber.

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